

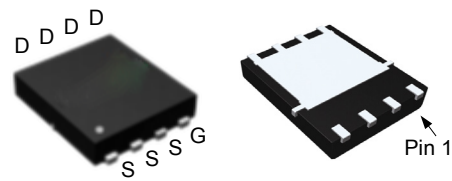
Features

- 40V/160A
 $R_{DS(ON)} = 1.8m\Omega (typ.) @ V_{GS} = 10V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)
- Moisture Sensitivity Level MSL1
 (per JEDEC J-STD-020D)

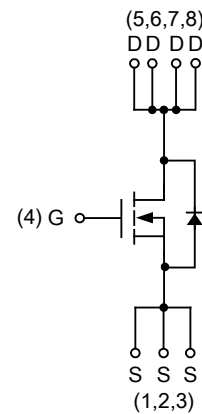
Applications

- Power Management in Desktop Computer or DC/DC Converters.

Pin Description



DFN5x6A-8_EP



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	
I _S	Diode Continuous Forward Current	T _C =25°C	160	A
I _D	Continuous Drain Current	T _C =25°C	160	A
		T _C =100°C	140	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	400	
P _D	Maximum Power Dissipation	T _C =25°C	115	W
		T _C =100°C	58	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	1.3	°C/W
I _D	Continuous Drain Current	T _A =25°C	28	A
		T _A =70°C	23	
I _{DM} ^a	Pulsed Drain Current	T _A =25°C	110	
P _D	Maximum Power Dissipation	T _A =25°C	2.7	W
		T _A =70°C	1.9	
R _{θJA} ^b	Thermal Resistance-Junction to Ambient	t ≤ 10s	20	°C/W
		Steady State	55	
I _{AS} ^c	Avalanche Current, Single pulse	L=0.1mH	65	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.1mH	211	mJ

Note * : Maximum continuous current is limited by bonding wire.

Note a : Pulse width limited by maximum junction temperature.

Note b : Surface mounted on 1in^2 pad area, steady state $t = 999\text{s}$.

Note c : UIS tested and pulse width limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

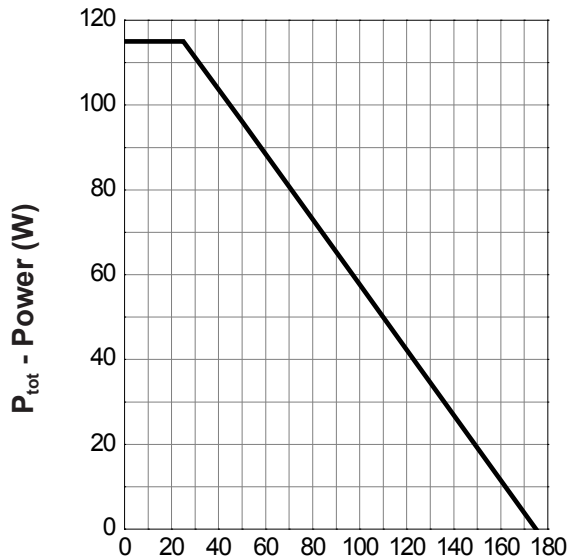
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

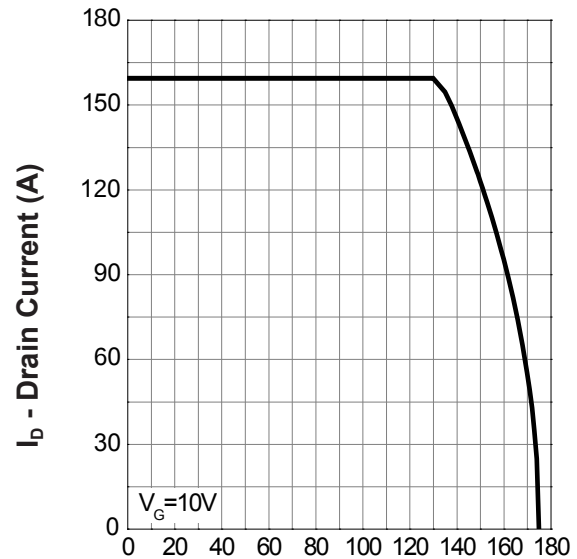
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =32V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A	-	1.8	2.2	mΩ
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =15A	-	38	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =25A, V _{GS} =0V	-	0.8	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =20A, dI _{SD} /dt=100A/μs	-	50	-	ns
t _a	Charge Time		-	26	-	
t _b	Discharge Time		-	23	-	
Q _{rr}	Reverse Recovery Charge		-	54	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1	2	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, Frequency=1.0MHz	-	4750	6175	pF
C _{oss}	Output Capacitance		-	1120	-	
C _{rss}	Reverse Transfer Capacitance		-	135	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, R _L =20Ω, I _{DS} =1A, V _{GEN} =6V, R _G =6Ω	-	30	54	ns
t _r	Turn-on Rise Time		-	12	22	
t _{d(OFF)}	Turn-off Delay Time		-	55	99	
t _f	Turn-off Fall Time		-	78	141	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _{DS} =20A	-	61	-	nC
Q _{gth}	Threshold Gate Charge		-	14	-	
Q _{gs}	Gate-Source Charge		-	22	-	
Q _{gd}	Gate-Drain Charge		-	8	-	

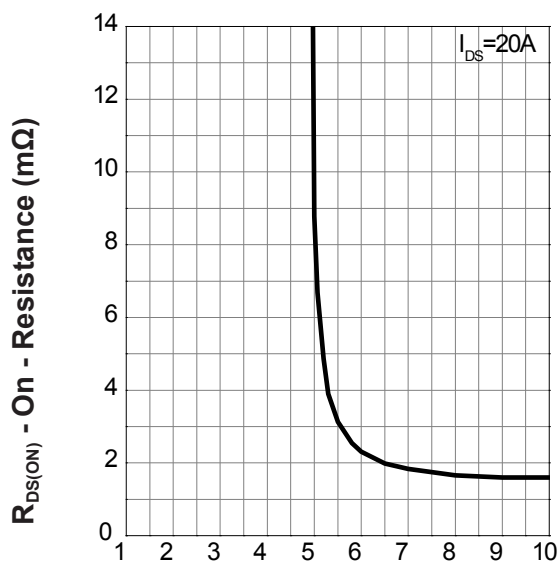
Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

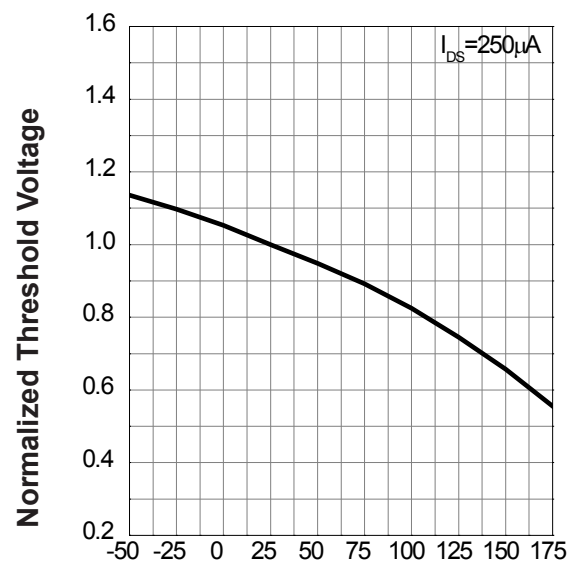
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

Power Dissipation

 T_c - Case Temperature (°C)

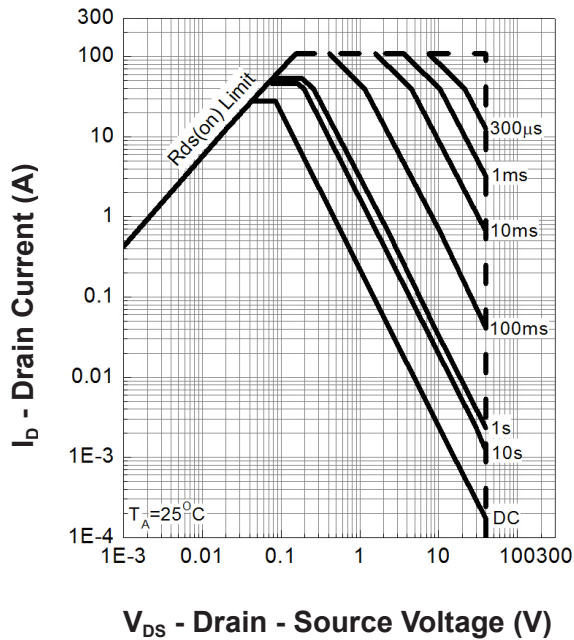
Drain Current

 T_c - Case Temperature (°C)

Gate-Source On Resistance

 V_{GS} - Gate - Source Voltage (V)

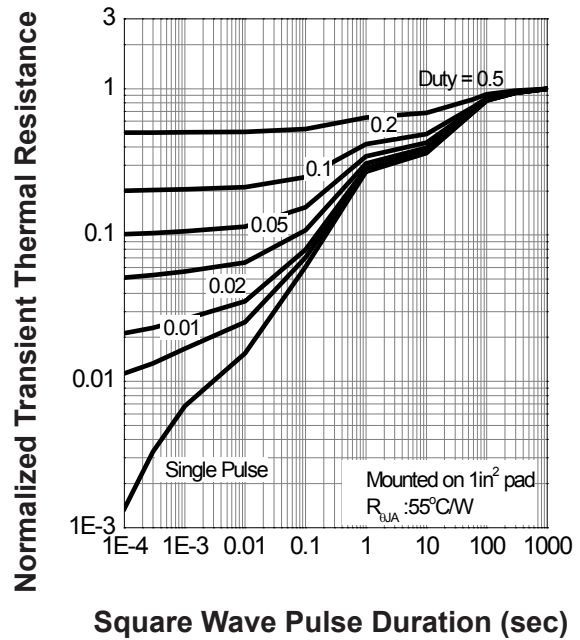
Gate Threshold Voltage

 T_J - Junction Temperature (°C)

Typical Operating Characteristics(Cont.)

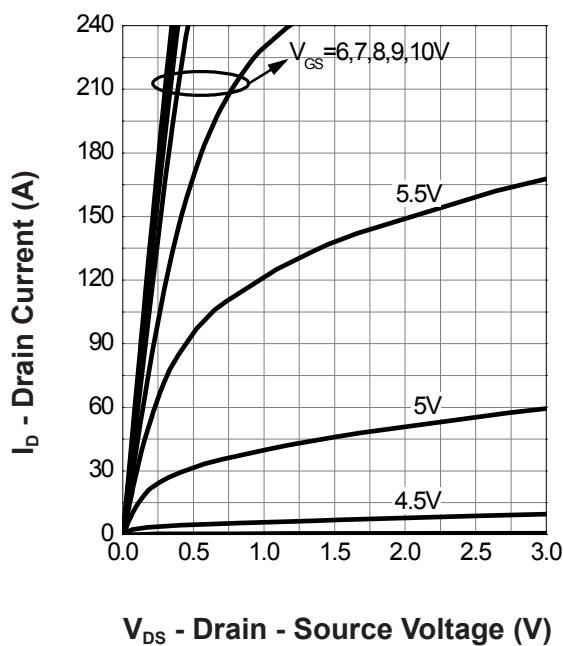
Safe Operation Area



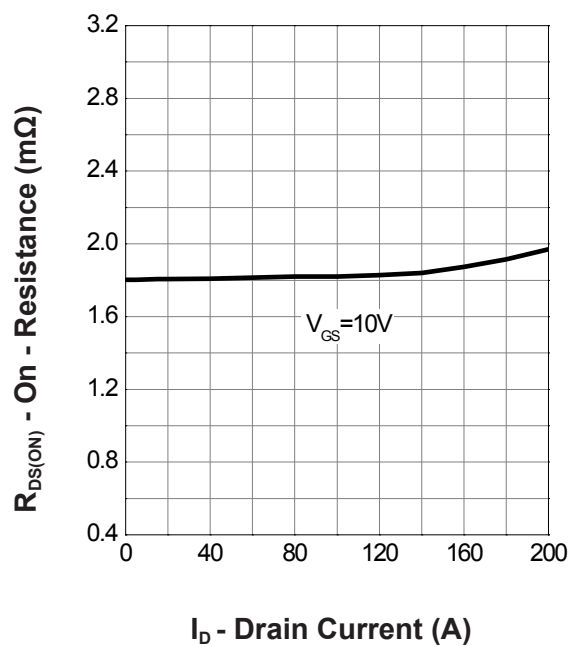
Thermal Transient Impedance



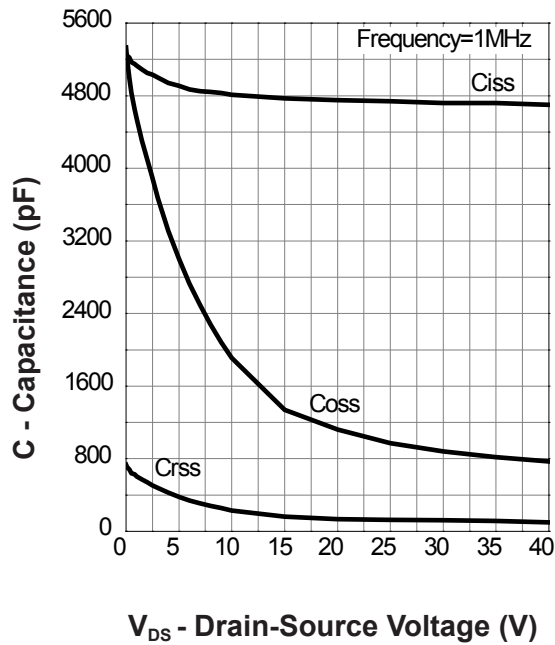
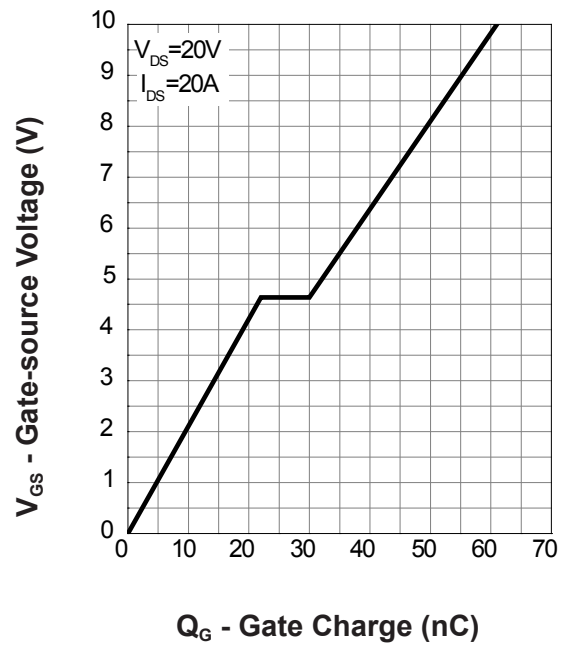
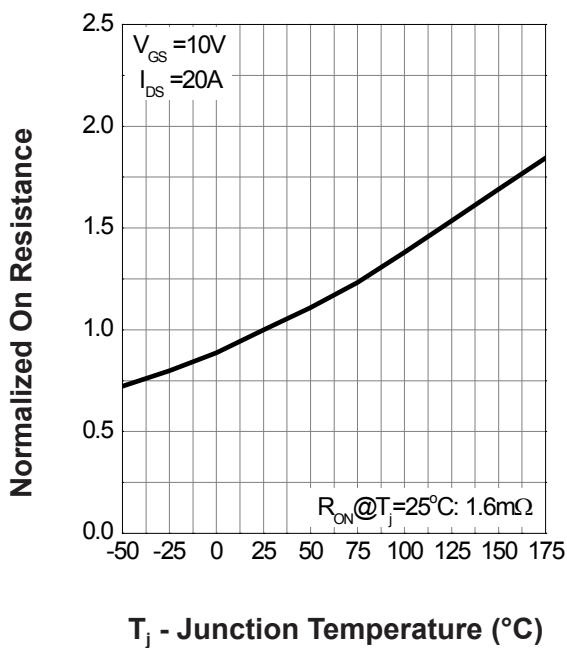
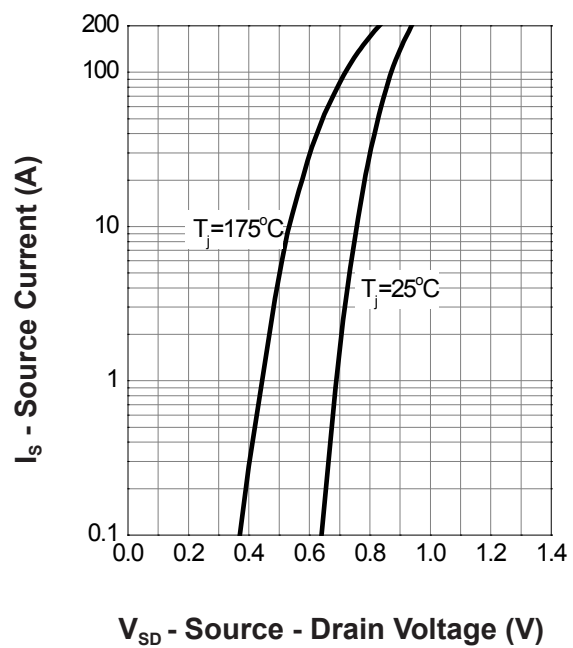
Output Characteristics



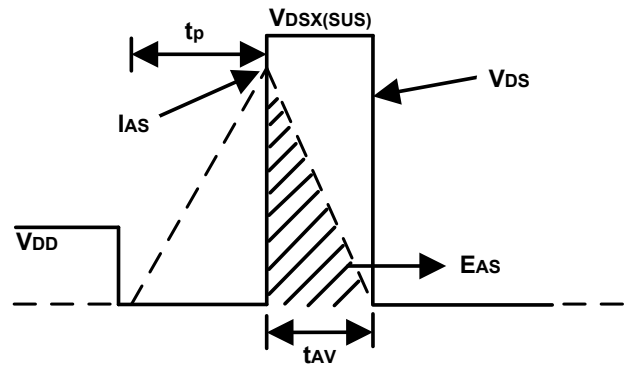
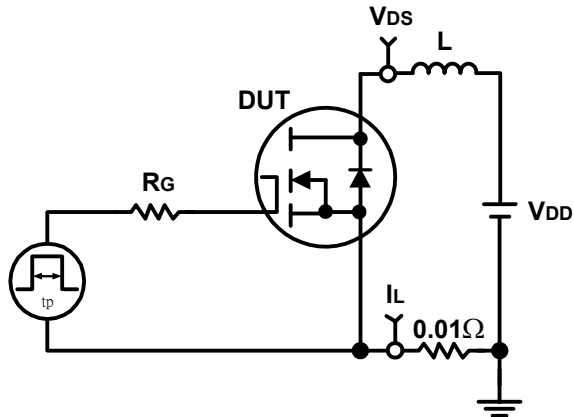
Drain-Source On Resistance



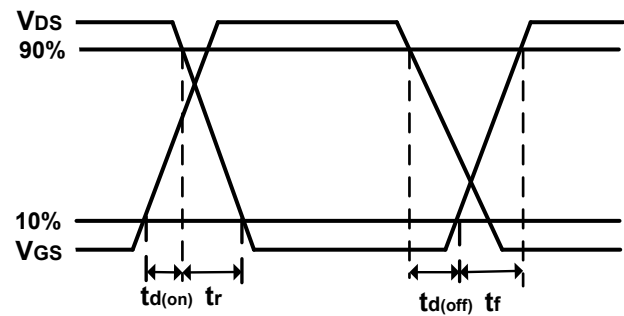
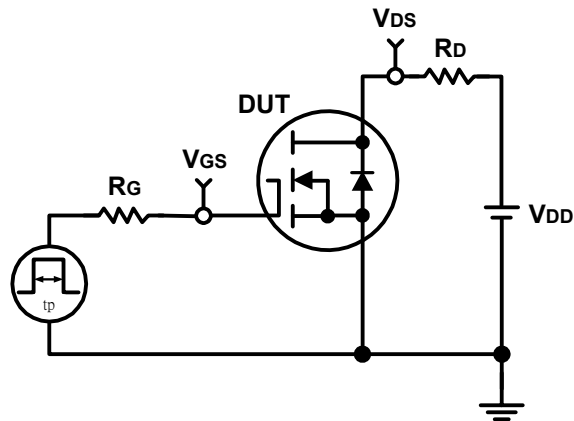
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

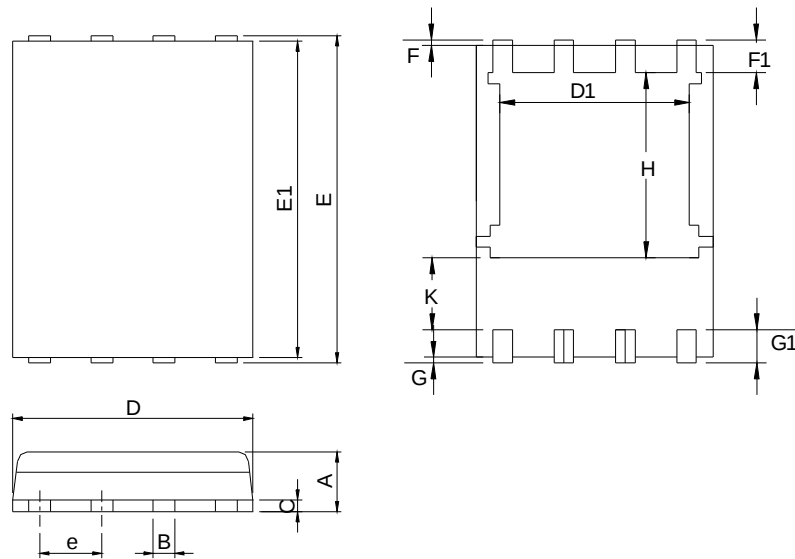


Switching Time Test Circuit and Waveforms



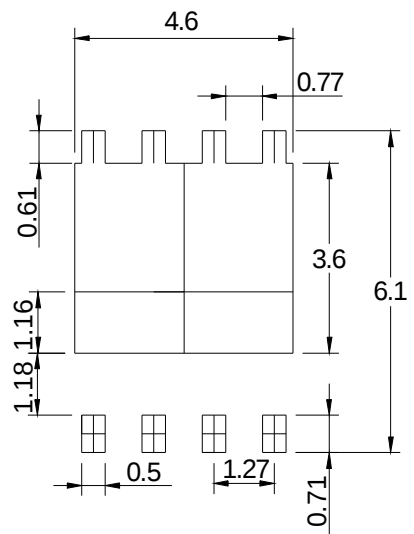
Package Information

DFN5x6-8



SYMBOL	DFN5x6-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

RECOMMENDED LAND PATTERN



UNIT: mm

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.
Mold flash or protrusions shall not exceed 10 mil.